



FAIRCHILD SEMICONDUCTOR TM

PN4250A



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
Vcbo	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		PN4250A		
PD	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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PNP General Purpose Amplifier

(continued)				
Min	Max	Units		

OFF CHARACTERISTICS

Symbol

Electrical Characteristics

Parameter

V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$	60		V
$V_{(\text{BR})\text{CES}}$	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \ \mu A, \ I_{\rm B} = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, \ I_C = 0$	5.0		V
Ісво	Collector-Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$		10	nA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		20	nA

 $TA = 25^{\circ}C$ unless otherwise noted

Test Conditions

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \mu\text{A}$	250	700	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$		0.25	V

SMALL SIGNAL CHARACTERISTICS

Cob	Output Capacitance	V _{CB} = 5.0 V, f = 1.0 MHz		6.0	pF
hfe	Small-signal Current Gain	V _{CE} = 5.0 V, I _C = 1.0 mA,	250	800	
hie	Input Impedance	f = 1.0 kHz	6.0	20	kΩ
hoe	Output Admittance		5.0	50	μmhos
hre	Voltage Feedback Ratio			10	x10 ⁻⁴
NF	Noise Figure	$\label{eq:VcE} \begin{array}{l} V_{CE} = 5.0 \ V, \ I_C = 250 \ \mu\text{A}, \\ R_S = 1.0 \ k\Omega, \ f = 1.0 \ k\text{Hz}, \\ B_W = 150 \ \text{Hz} \\ V_{CE} = 5.0 \ V, \ I_C = 20 \ \mu\text{A}, \\ R_S = 10 \ k\Omega, \ f = 1.0 \ \text{kHz}, \\ B_W = 150 \ \text{Hz} \end{array}$		2.0 2.0	dB dB

*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

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